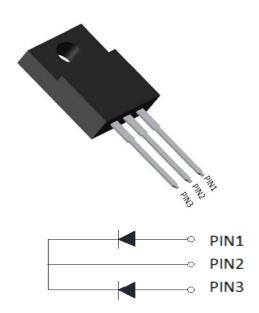


Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: ITO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102
• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

-maximum ramingo (ra = 0 - 0 mass saretimes specimes)						
PARAMETER	SYMBOL	UNIT	MBR30100FCT	MBR30150FCT	MBR30200FCT	
Device marking code			MBR30100FCT	MBR30150FCT	MBR30200FCT	
Repetitive Peak Reverse Voltage	VRRM	V	100	150	200	
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25°C	Ю	А		30		
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25℃	IFSM	А	250			
Current Squared Time @1ms≤t<8.3ms Tj=25°C,	l ² t	A ² s	259			
Storage Temperature	T _{stg}	$^{\circ}$	-55 ~ +175			
Junction Temperature	Tj	$^{\circ}$	-55 ~ +175			

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR30100FCT	MBR30150FCT	MBR30200FCT
Maximum instantaneous forward voltage drop per diode	VFM	٧	IFM=15.0A	0.8	0.85	0.9
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1		VRM=VRRM T _a =25℃	0.1		
	IRRM2	mA	VRM=VRRM T _a =125℃	20		

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	MBR30100FCT	MBR30150FCT	MBR30200FCT
Thermal Resistance	Between junction and case	РθЈ-С	°C /W		4.0	



■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR30100FCT THRU MBR30200FCT	Approximate 1.6	50	1000	5000	Tube

■Characteristics (Typical)

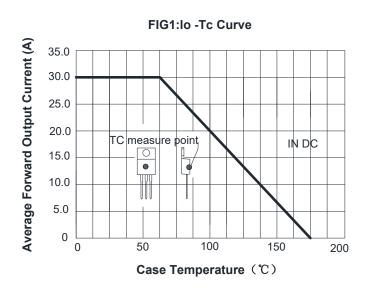
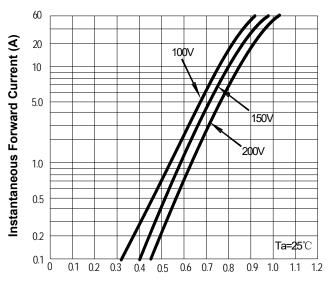


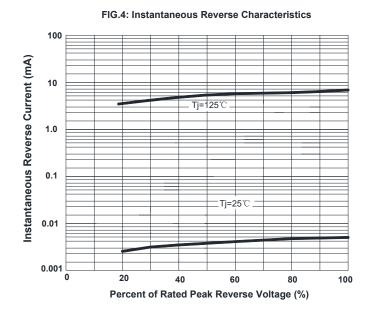
FIG2:Surge Forward Current Capability 300 Peak Forward Surge Current (A) 250 200 8.3ms Single Half Sine-Wave 150 JEDEC Method 100 50 0 20 2 5 50 100 10

Number of Cycles

FIG3: Forward Voltage

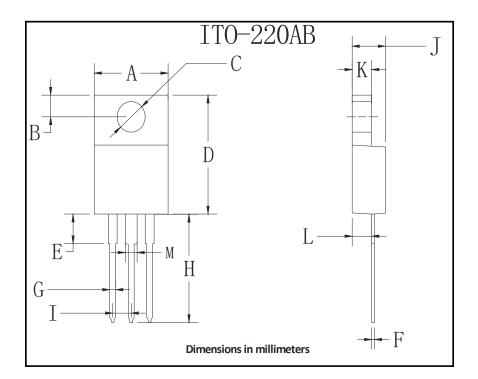


Instantaneous Forward Voltage (V)





■Outline Dimensions



ITO-220AB					
Dim	Min	Max			
Α	9.8	10.2			
В	2.25	2.75			
С	2.95	3.45			
D	14.75	15.25			
E	3.05	3.95			
F	0.45	0.75			
G	0.45	0.75			
Н	13.4	14.2			
I	2.35	2.75			
J	4.3	4.8			
K	2.58	2.82			
L	2.58	2.82			
М	1.47	1.77			



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